ANALOG DEVICES
AHEAD OF WHAT'S POSSIBLE™

SUMMARY OF CHANGE (DIRECT BUMP)

	From	To	Remarks
Bumping Site	ASE Kaohsiung (AEG)	Chip Bond KF (CB4)	Site Change
PI-1	10um	10 um	-
UBM	Ti(0.2)/NiV(0.3)/Cu(0.8)	Ti(0.2)/Cu(0.4)/Cu(8)	Seed layer change (NiV to Cu)
Bump Composition	95.5Sn_4.0Ag_0.5Cu	95.5Sn_4.0Ag_0.5Cu	-
Final Bump Height	240 um	240 um	-
Backgrind	ASE Kaohsiung (AEG)	Chip Bond KF (CB4)	Site Change
Laser Marking	ASE Kaohsiung (AEG)	Chip Bond KF (CB4)	Site Change

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SUMMARY OF CHANGE (CU RDL BUMP)

	From	To	Remarks
Bumping Site	ASE Kaohsiung (AEG)	Chip Bond KF (CB4)	Site Change
PI-1	5um	5 um	-
RDL	Ti(0.2)/Al(1.5)/Ti(0.2)	TiW(0.32)/Cu(0.2)/Cu(3)	RDL Met. Change
PI-2	5um	5 um	-
UBM	Al(0.4)/NiV(0.3)/Cu(0.8)	Ti(0.2)/Cu(0.4)/Cu(8.6)	Seed Layer Change
Bump Composition	96.8Sn_2.6Ag_0.6Cu	95.5Sn_4.0Ag_0.5Cu	SAC266 to SAC405
Final Bump Height	200 um	200 um	-
Backgrind	ASE Kaohsiung (AEG)	Chip Bond KF (CB4)	Site Change
Laser Marking	ASE Kaohsiung (AEG)	Chip Bond KF (CB4)	Site Change